GCS InGaAs PIN Photodiodes for 1-4 Gb/sec Applications

1310/1550 nm InGaAs PIN PD

- Planar Diode on n+ InP Substrates
- Anode Bonding Pad on Front Side, Cathode on backside
- Low Dark Current & Capacitance with High Responsivity
- Bandwidths up to 4GHz
- Customer Specified Configurations Available

Applications

- 1.25G EPON
- Short Reach Optical Networks
- 1 to 4 Gigabit Ethernet, Fiber Channel, CATV

Key Benefits

- 4-inch Wafer Manufacturing
- Fast Cycle-Times
- CAD Support & Mask Procurement
- Robust Process

Mask ID: Do105

<table>
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<tr>
<th>CHARACTERISTICS</th>
<th>Conditions</th>
<th>Min.</th>
<th>Typical</th>
<th>Max</th>
<th>Unit</th>
<th>Notes</th>
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<td>Bandwidth</td>
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PHYSICAL

- Aperture Dia. 68 µm
- Bonding Pad Dia. 80 µm
- Die Height 100-150 µm
- Die Size 250 µm X 310 µm
- Substrate n+ InP

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